NEC

PNP SILICON TRANSISTOR 2SA915

DESCRIPTION

The 2SA915 is designed for use in driver stages of audio

frequency amplifiers.

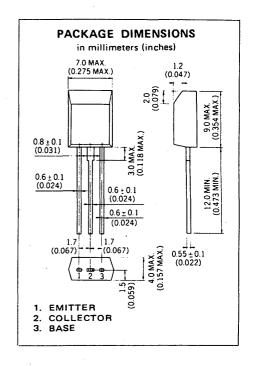
FEATURES

• High Total Power Dissipation and High Breakdown Voltage:

1.0 W at 25 °C Ambient Temperature/V_{CEO} = -120 V

• Complementary to the NEC-2SC1940 NPN Transistor.

ABSOLUTE MAXIMUM RATINGS



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

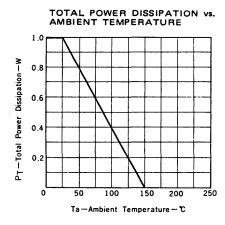
SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1	DC Current Gain	90	200	400	_	V _{CE} = -10 V, I _C = -10 mA
hFE2	DC Current Gain	50	200		-	$V_{CE} = -10 \text{ V}, I_{C} = -1.0 \text{ mA}$
fT	Gain Bandwidth Product	50	80		MHz	$V_{CE} = -10 \text{ V, I}_{E} = 10 \text{ mA}$
C _{ob}	Output Capacitance		2.5	3.5	pF	$V_{CB} = -10 \text{ V, I}_{E} = 0, f = 1.0 \text{ MHz}$
1 _{CBO}	Collector Cutoff Current			-100	nA	$V_{CB} = -120 \text{ V, } I_E = 0$
IEBO	Emitter Cutoff Current			-100	nA	$V_{EB} = -5.0 \text{ V, I}_{C} = 0$
VBE	Base to Emitter Voltage	-650	-695	-750	mV	$V_{CE} = -10 \text{ V, I}_{C} = -10 \text{ mA}$
V _{CE(sat)}	Collector Saturation Voltage		-0.18	-0.6	V	$I_C = -20 \text{ mA}, I_B = -2.0 \text{ mA}$
V _{BE(sat)}	Base Saturation Voltage		-0.79	-1.0	V	I _C = -20 mA, I _B = -2.0 mA

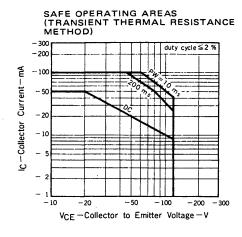
Classification of hFE1

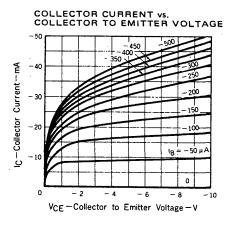
Rank	М	L	К
Range	90 – 180	135 — 270	200 – 400

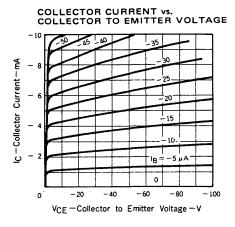
h_{FE1} Test Conditions: $V_{CE} = -10 \text{ V}$, $I_{C} = -10 \text{ mA}$

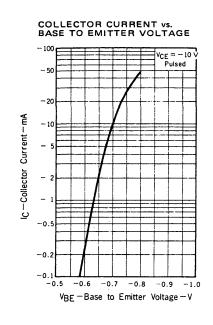
TYPICAL CHARACTERISTICS (Ta=25 °C unless otherwise noted)

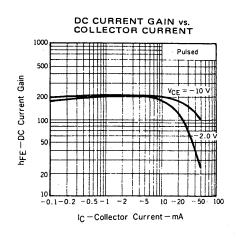


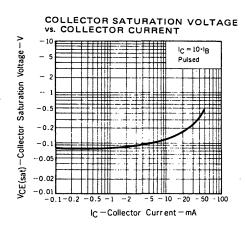


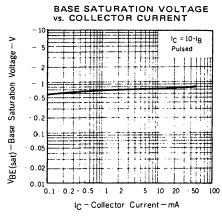


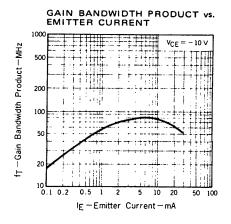




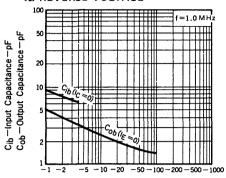












V_{CB} - Collector to Base Voltage - V V_{EB} - Emitter to Base Voltage - V